

- L1: (1806) semiconductor and hydrogen near anneal\$3
- L2: (141) semiconductor and hydrogen near anneal\$31 and polysilicon and gates
- L3: (17) semiconductor and hydrogen near anneal\$31 and polysilicon and floating near gates
- L4: (22) 2 and (anneal\$3 with (polysilicon and gate\$1))
- L5: (603) semiconductor and hydrogen near anneal\$31 and polysilicon
- L6: (13) 5 and anneal\$3 near polysilicon

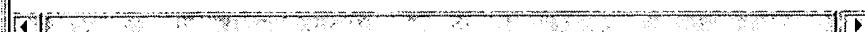
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5 and anneal\$3 near polysilicon

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U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	US 20040164297 A1	20040826	20	Display device	257/59	257/E21.413; 257/E21.703; 257/E27.111;
2	<input type="checkbox"/>	US 20040132270 A1	20040708	10	METHOD OF FORMING A NOVEL GATE ELECTRODE STRUCTURE COMPRISED OF A SILICON-GERMANIUM LAYER LOCATED BETWEEN THE	438/585	257/E21.198; 257/E29.155;
3	<input type="checkbox"/>	US 20040056297 A1	20040325	24	Substrate device, method of manufacturing the same, electro-optical device, and electronic	257/306	438/197; 438/30
4	<input type="checkbox"/>	US 20020070388 A1	20020613	9	LATERAL POLYSILICON PIN DIODE AND METHOD FOR SO FABRICATING	257/122	257/124; 257/141; 257/146;
5	<input type="checkbox"/>	US 20010052626 A1	20011220	9	Method for fabricating dual-gate structure	257/412	257/E21.632
6	<input type="checkbox"/>	US 6780741 B2	20040824	10	Method of forming a novel gate electrode structure comprised of a silicon-germanium layer located between random-drained polysilicon layers	438/592	257/E21.198; 257/E29.155;
7	<input type="checkbox"/>	US 6426547 B1	20020730	8	Lateral polysilicon pin diode and method for so fabricating	257/656	438/658; 257/67; 257/75;
8	<input type="checkbox"/>	US 6084276 A	20000704	24	Threshold voltage tailoring of corner of MOSFET device	257/397	257/E29.336;
9	<input type="checkbox"/>	US 5994202 A	19991130	24	Threshold voltage tailoring of the corner of a MOSFET device	438/433	257/394; 257/404;
10	<input type="checkbox"/>	US 5424230 A	19950613	9	Method of manufacturing a polysilicon thin film transistor	438/166	257/513; 257/354;
11	<input type="checkbox"/>	US 5111260 A	19920505	16	Polysilicon FETs	257/347	257/374; 257/386;